



Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from,Europe,America and south Asia,supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of "Quality Parts,Customers Priority,Honest Operation,and Considerate Service",our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



## Contact us

Tel: +86-755-8981 8866 Fax: +86-755-8427 6832

Email & Skype: info@chipsmall.com Web: www.chipsmall.com

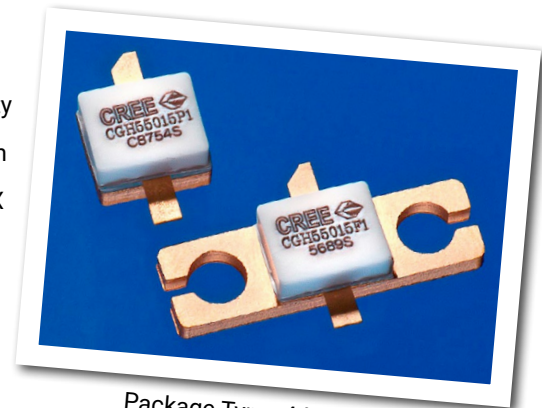
Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China



# CGH55015F1 / CGH55015P1

15 W, 5500-5800 MHz, GaN HEMT for WiMAX

Cree's CGH55015F1/CGH55015P1 is a gallium nitride (GaN) high electron mobility transistor (HEMT) designed specifically for high efficiency, high gain and wide bandwidth capabilities, which makes the CGH55015F1/CGH55015P1 ideal for 5.5-5.8 GHz WiMAX and linear amplifier applications. The transistor is available in both screw-down, flange and solder-down, pill packages. Based on appropriate external match adjustment, the CGH55015F1/CGH55015P1 is suitable for 4.9 - 5.5 GHz applications as well.



Package Type: 440196 & 440166  
PN: CGH55015P1 & CGH55015F1

## Typical Performance 5.5-5.8GHz ( $T_c = 25^\circ\text{C}$ )

Parameter	5.50 GHz	5.65 GHz	5.80 GHz	Units
Small Signal Gain	10.7	11.0	10.7	dB
EVM at $P_{AVE} = 23$ dBm	1.9	1.8	2.0	%
EVM at $P_{AVE} = 33$ dBm	1.5	1.5	1.7	%
Drain Efficiency at $P_{AVE} = 33$ dBm	25	25	25	%
Input Return Loss	11.5	14.5	10.5	dB

**Note:**

Measured in the CGH55015-AMP amplifier circuit, under 802.16 OFDM, 3.5 MHz Channel BW, 1/4 Cyclic Prefix, 64 QAM Modulated Burst, 5 ms Burst, Symbol Length of 59, Coding Type RS-CC, Coding Rate Type 2/3, PAR = 9.8 dB @ 0.01 % Probability on CCDF.

## Features



- 5.5 - 5.8 GHz Operation
- 15 W Peak Power Capability
- >10.5 dB Small Signal Gain
- 2 W  $P_{AVE} < 2.0$  % EVM
- 25 % Efficiency at 2 W Average Power
- Designed for WiMAX Fixed Access 802.16-2004 OFDM Applications
- Designed for Multi-carrier DOCSIS Applications

Large Signal Models Available for ADS and MWO

## Absolute Maximum Ratings (not simultaneous) at 25°C Case Temperature

Parameter	Symbol	Rating	Units	Conditions
Drain-Source Voltage	$V_{DS}$	84	Volts	25°C
Gate-to-Source Voltage	$V_{GS}$	-10, +2	Volts	25°C
Power Dissipation	$P_{DISS}$	7	Watts	
Storage Temperature	$T_{STG}$	-65, +150	°C	
Operating Junction Temperature	$T_J$	225	°C	
Maximum Forward Gate Current	$I_{GMAX}$	4.0	mA	25°C
Maximum Drain Current <sup>1</sup>	$I_{DMAX}$	1.5	A	25°C
Soldering Temperature <sup>2</sup>	$T_S$	245	°C	
Screw Torque	$\tau$	60	in-oz	
Thermal Resistance, Junction to Case <sup>3</sup>	$R_{\theta JC}$	8.0	°C/W	85°C
Case Operating Temperature <sup>3</sup>	$T_C$	-40, +150	°C	

Note:

<sup>1</sup> Current limit for long term, reliable operation.

<sup>2</sup> Refer to the Application Note on soldering at [www.cree.com/RF/Document-Library](http://www.cree.com/RF/Document-Library)

<sup>3</sup> Measured for the CGH55015 at  $P_{DISS} = 7W$ .

## Electrical Characteristics ( $T_C = 25^\circ C$ )

Characteristics	Symbol	Min.	Typ.	Max.	Units	Conditions
<b>DC Characteristics<sup>1</sup></b>						
Gate Threshold Voltage	$V_{GS(th)}$	-3.8	-3.0	-2.3	$V_{DC}$	$V_{DS} = 10 V, I_D = 3.6 mA$
Gate Quiescent Voltage	$V_{GS(Q)}$	-	-2.7	-	$V_{DC}$	$V_{DS} = 28 V, I_D = 115 mA$
Saturated Drain Current	$I_{DS}$	2.9	3.5	-	A	$V_{DS} = 6.0 V, V_{GS} = 2.0 V$
Drain-Source Breakdown Voltage	$V_{BR}$	120	-	-	$V_{DC}$	$V_{GS} = -8 V, I_D = 3.6 mA$
<b>RF Characteristics<sup>2,3</sup> (<math>T_C = 25^\circ C, F_0 = 5.65 GHz</math> unless otherwise noted)</b>						
Small Signal Gain	$G_{SS}$	8.5	11.0	-	dB	$V_{DD} = 28 V, I_{DQ} = 115 mA$
Drain Efficiency <sup>4</sup>	$\eta$	20.6	25	-	%	$V_{DD} = 28 V, I_{DQ} = 115 mA, P_{AVE} = 2.0 W$
Error Vector Magnitude	EVM	-	2.0	2.5	%	$V_{DD} = 28 V, I_{DQ} = 115 mA, P_{AVE} = 2.0 W$
Output Mismatch Stress	VSWR	-	-	10 : 1	$\Psi$	No damage at all phase angles, $V_{DD} = 28 V, I_{DQ} = 115 mA,$ $P_{AVE} = 2.0 W$
<b>Dynamic Characteristics</b>						
Input Capacitance	$C_{GS}$	-	4.5	-	pF	$V_{DS} = 28 V, V_{GS} = -8 V, f = 1 MHz$
Output Capacitance	$C_{DS}$	-	1.3	-	pF	$V_{DS} = 28 V, V_{GS} = -8 V, f = 1 MHz$
Feedback Capacitance	$C_{GD}$	-	0.2	-	pF	$V_{DS} = 28 V, V_{GS} = -8 V, f = 1 MHz$

Notes:

<sup>1</sup> Measured on wafer prior to packaging.

<sup>2</sup> Measured in the CGH55015-AMP test fixture.

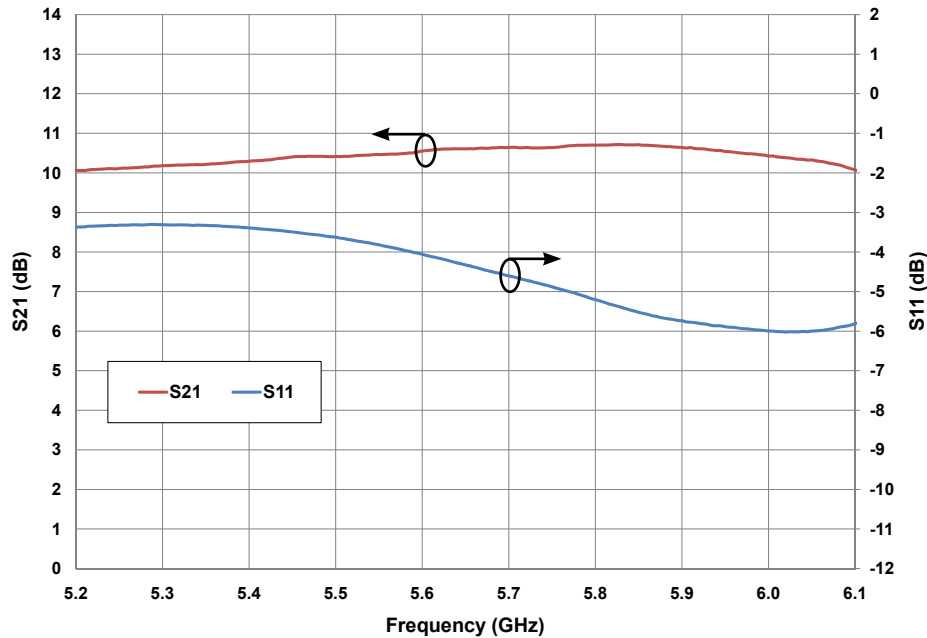
<sup>3</sup> Under 802.16 OFDM, 3.5 MHz Channel BW, 1/4 Cyclic Prefix, 64 QAM Modulated Burst, 5 ms Burst, Symbol Length of 59, Coding Type RS-CC, Coding Rate Type 2/3, PAR = 9.8 dB @ 0.01 % Probability on CCDF.

<sup>4</sup> Drain Efficiency =  $P_{OUT} / P_{DC}$

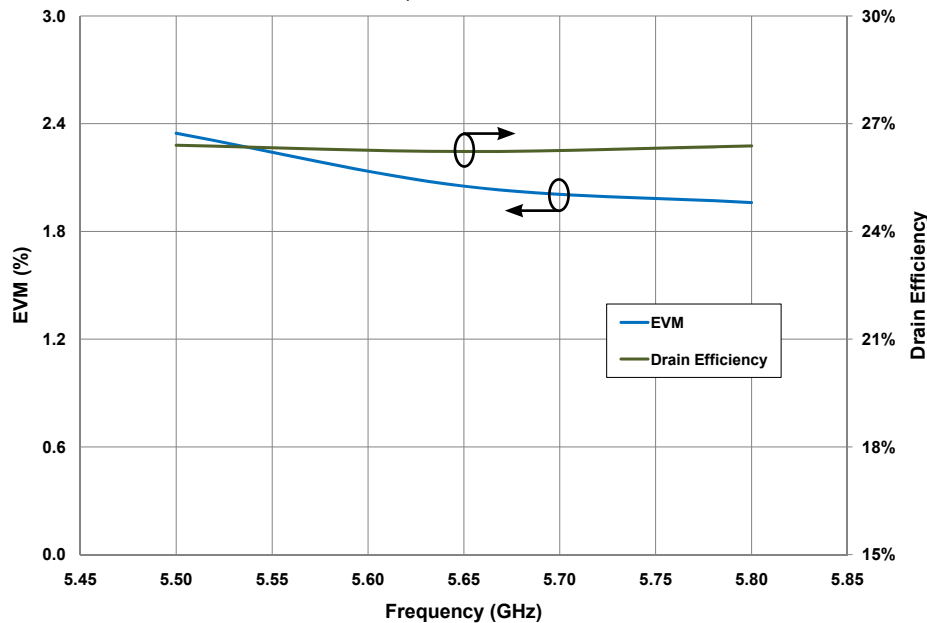


## Typical WiMAX Performance

Small Signal S-Parameters vs Frequency measured  
in the CGH55015-AMP  
 $V_{DD} = 28\text{ V}$ ,  $I_{DQ} = 115\text{ mA}$



EVM and Efficiency vs. Frequency measured  
in the CGH55015-AMP  
 $V_{DD} = 28\text{ V}$ ,  $I_{DQ} = 115\text{ mA}$ ,  $P_{OUT} = 2.5\text{ W}$

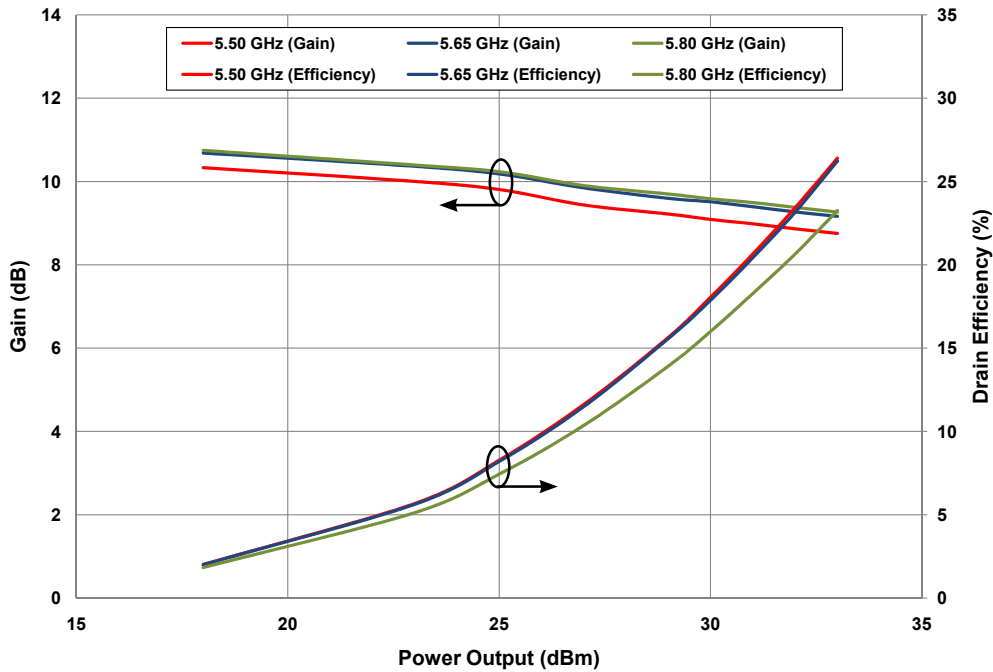


Note:

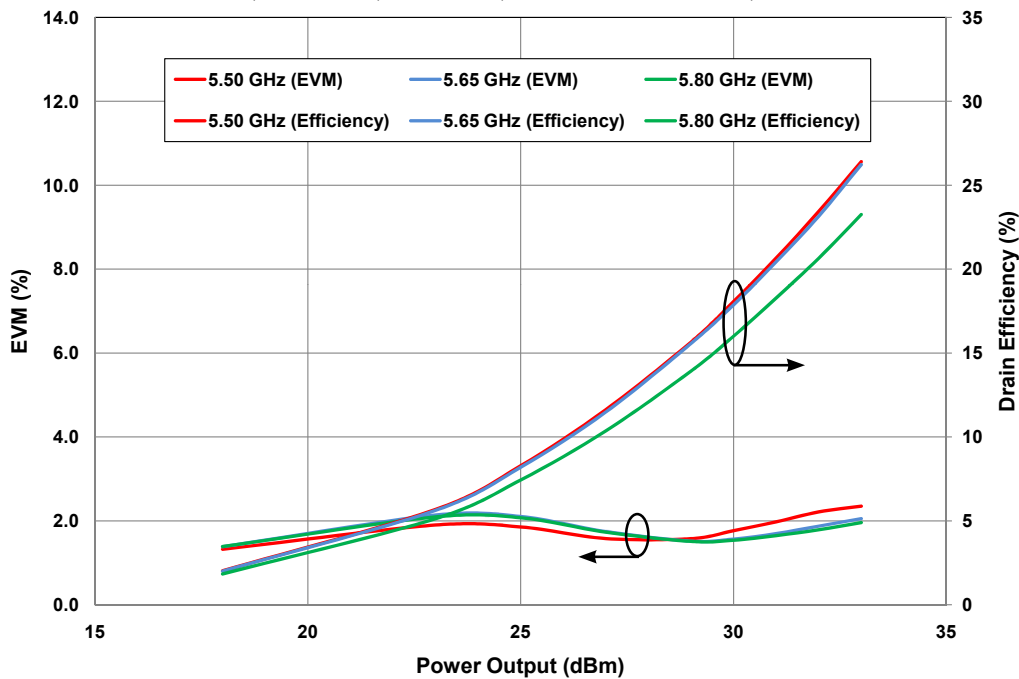
Under 802.16 OFDM, 3.5 MHz Channel BW, 1/4 Cyclic Prefix, 64 QAM Modulated Burst, Symbol Length of 59, Coding Type RS-CC, Coding Rate Type 2/3, PAR = 9.8 dB @ 0.01 % Probability on CCDF.

## Typical WiMAX Performance

**Drain Efficiency and Gain vs Power Output measured in the CGH55015-AMP**  
 $V_{DD} = 28\text{ V}$ ,  $I_{DQ} = 115\text{ mA}$ , 802.16-2004 OFDM, PAR = 9.8 dB



**Typical EVM and Drain Efficiency vs Output Power measured in the CGH55015-AMP at 5.50 GHz, 5.65 GHz, 5.80 GHz, 802.16-2004 OFDM, PAR=9.8 dB**

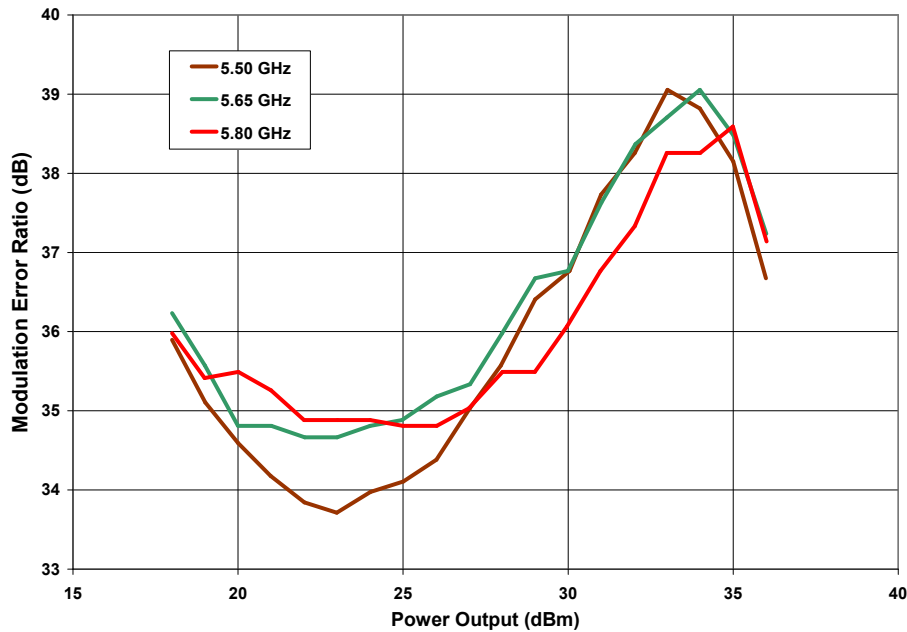


**Note:**

Under 802.16 OFDM, 3.5 MHz Channel BW, 1/4 Cyclic Prefix, 64 QAM Modulated Burst, Symbol Length of 59, Coding Type RS-CC, Coding Rate Type 2/3, PAR = 9.8 dB @ 0.01 % Probability on CCDF.

## Typical DOCSIS Performance

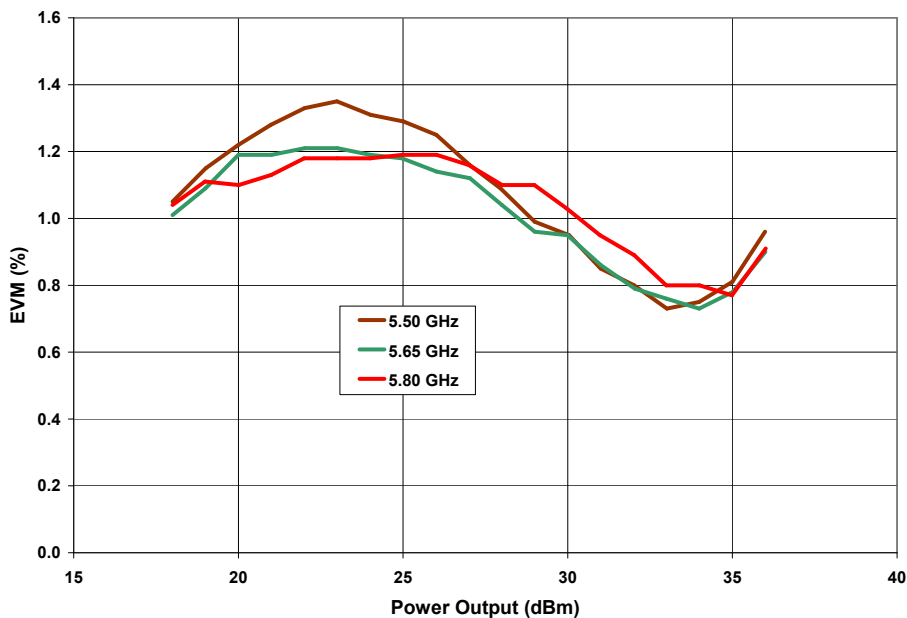
### DOCSIS Modulation Error Ratio vs Output Power of CGH55015



Note:

MER is the metric of choice for cable systems and can be related to EVM by the following equation:  $EVM(\%) = 100 \times 10^{-((MER_{dB} + MTA_{dB})/20)}$ . MTA is the "maximum-to-average constellation power ratio" which varies with the modulation type: MTA = 0 for BPSK and QPSK; 2.55 for 16QAM and 8QAM-DS; 3.68 for 64QAM and 32QAM-DS; 4.23 for 256QAM and 128QAM-DS

### DOCSIS EVM vs Output Power of CGH55015 in Broadband Amplifier Circuit

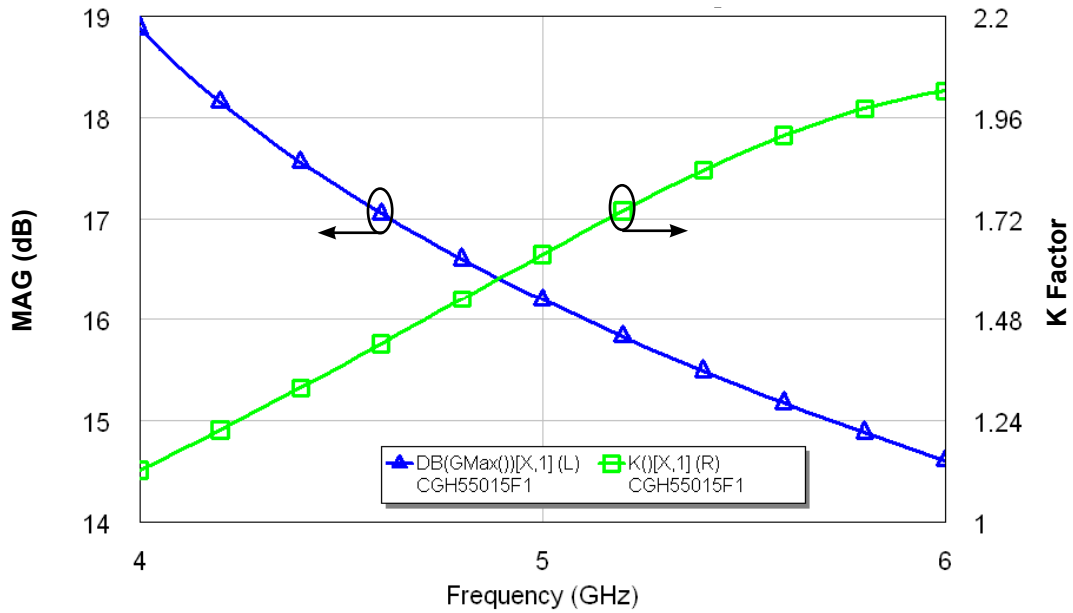


Note:

Under DOCSIS, 6.0 MHz Channel BW, 64 QAM, PN23, Filter Alpha 0.18, PAR = 6.7dB.

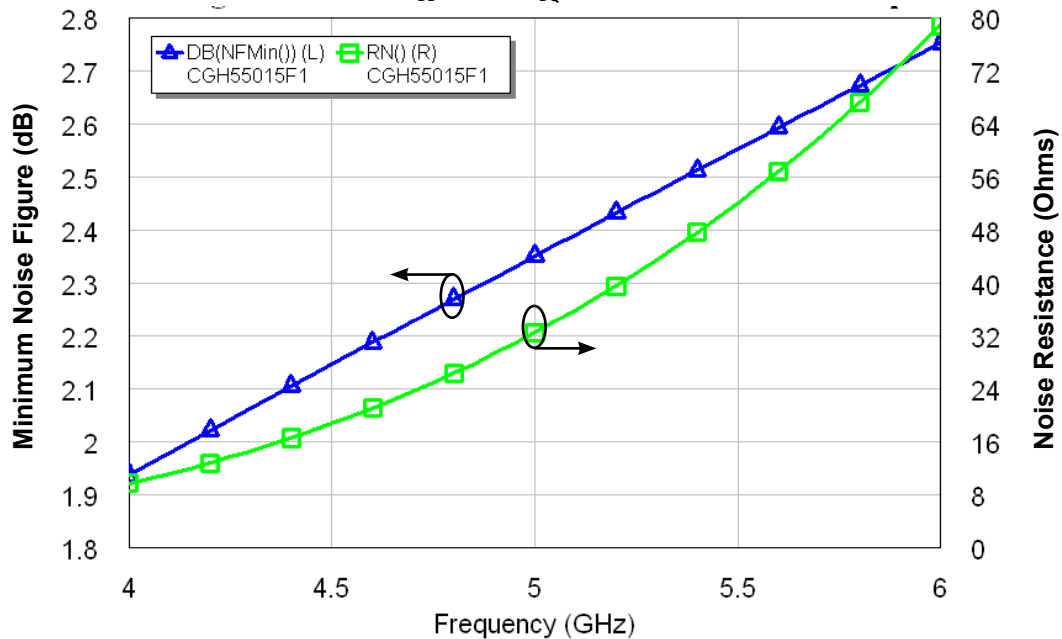
## Typical Performance

**Simulated Maximum Available Gain and K Factor of the CGH55015F1/P1**  
 $V_{DD} = 28\text{ V}, I_{DQ} = 115\text{ mA}$

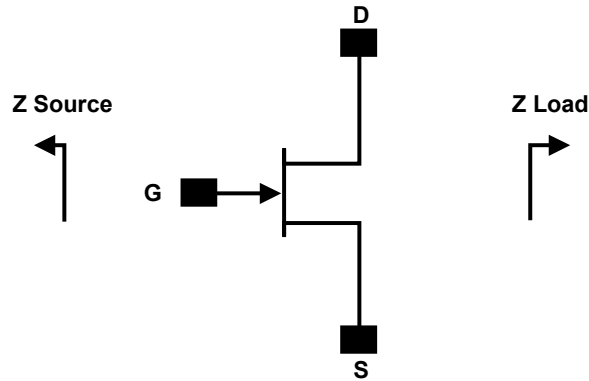


## Typical Noise Performance

**Simulated Minimum Noise Figure and Noise Resistance vs Frequency of the CGH55015F1/P1**  
 $V_{DD} = 28\text{ V}, I_{DQ} = 115\text{ mA}$



## Source and Load Impedances



Frequency (MHz)	Z Source	Z Load
5500	8.7 - j30.2	21.6 - j4.7
5650	10.2 - j26.9	24.2 - j5.5
5800	12.3 - j24.3	26.5 - j7.5

Note 1.  $V_{DD} = 28V$ ,  $I_{DQ} = 115\text{ mA}$  in the 440166 package.

Note 2. Impedances are extracted from the CGH55015-AMP demonstration amplifier and are not source and load pull data derived from the transistor.

## Electrostatic Discharge (ESD) Classifications

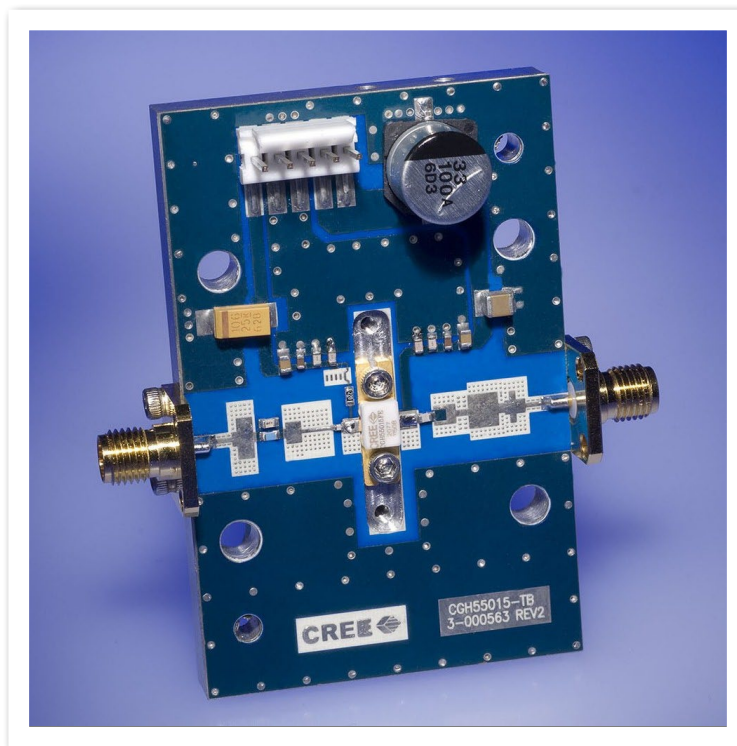
Parameter	Symbol	Class	Test Methodology
Human Body Model	HBM	1A > 250 V	JEDEC JESD22 A114-D
Charge Device Model	CDM	1 < 200 V	JEDEC JESD22 C101-C



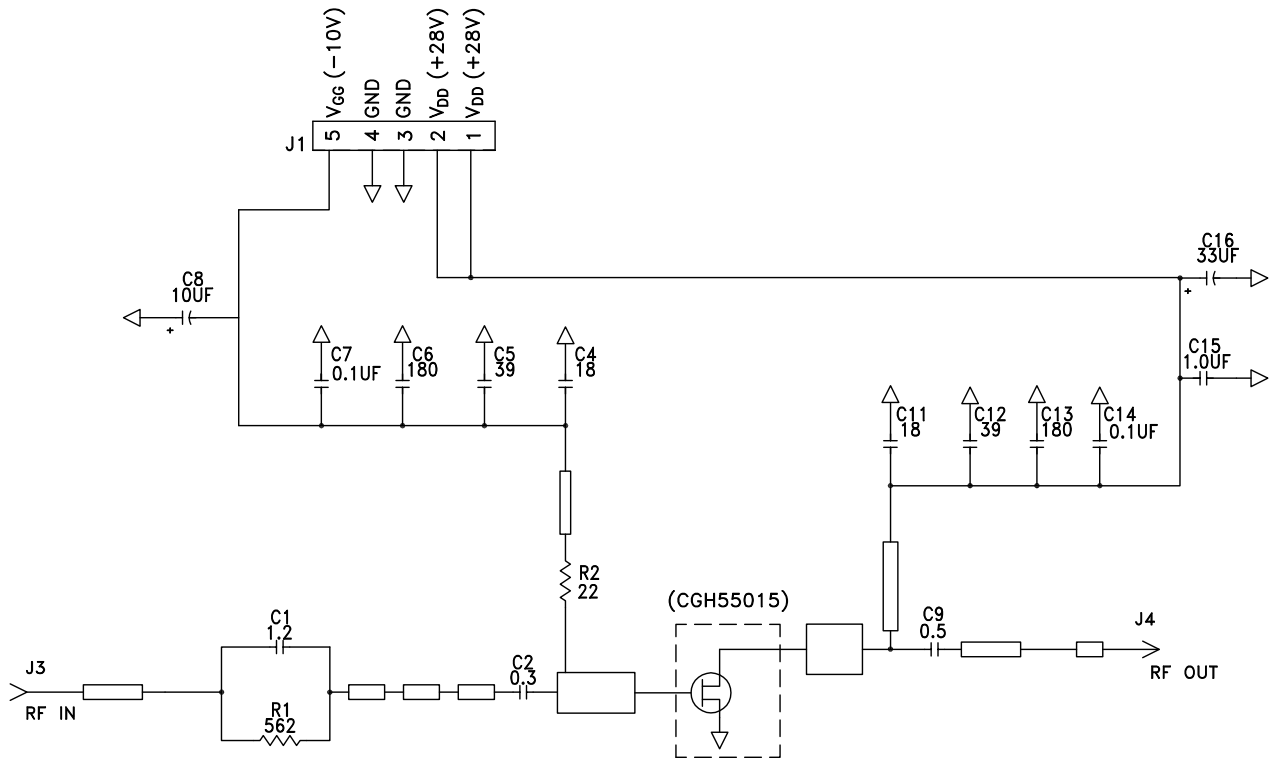
## CGH55015-AMP1 Demonstration Amplifier Circuit Bill of Materials

Designator	Description	Qty
C1	CAP, 1.2pF, +/-0.1 pF, 0603, ATC 600S	1
C2	CAP, 0.3pF, +/-0.05 pF, 0402, ATC 600L	1
C9	CAP, 0.5pF,+/-0.05pF, 0603, ATC 600S	1
C4,C11	CAP, 18pF, +/-5%, 0603, ATC 600S	2
C5,C12	CAP, 39pF +/-5%, 0603, ATC 600S	2
C6,C13	CAP, CER, 180pF, 50V, +/-5%, C0G, 0603	2
C7,C14	CAP, CER, 0.1UF, 50V, +/-10%, X7R, 0805	2
C8	CAP, 10UF, 16V, SMT, TANTALUM	1
C15	CAP, 1.0UF ±10%, 100V, 1210, X7R	1
C16	CAP, 33UF, 100V, ELECT, FK, SMD	1
R1	RES, 1/16W, 0603, 1%, 562 OHMS	1
R2	RES, 1/16W, 0603, 1%, 22 OHMS	1
J1	HEADER RT> PLZ .1 CEN LK 5 POS	1
J3,J4	CONN, SMA, FLANGE	2
-	PCB, RO4350B, Er = 3.48, h = 20 mil	1
-	CGH55015	1

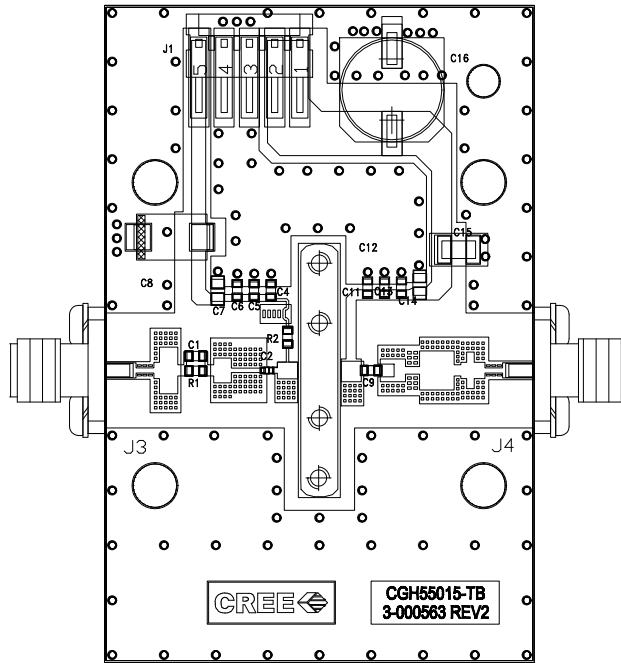
## CGH55015-AMP Demonstration Amplifier Circuit



## CGH55015-AMP Demonstration Amplifier Circuit Schematic



## CGH55015-AMP Demonstration Amplifier Circuit Outline

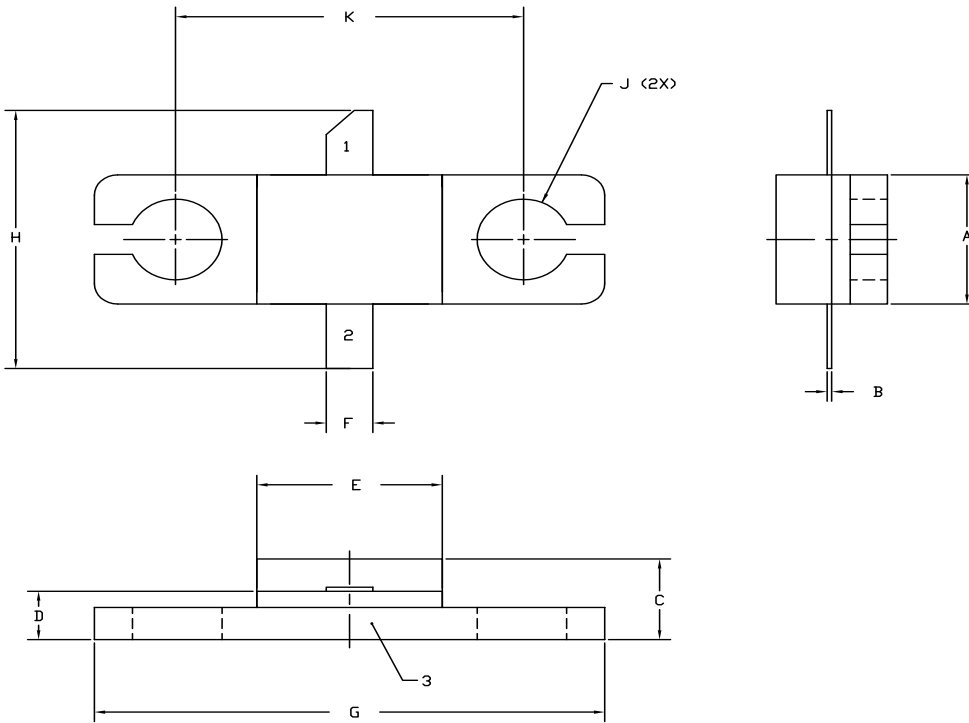


**Typical Package S-Parameters for CGH55015**  
 (Small Signal,  $V_{DS} = 28\text{ V}$ ,  $I_{DQ} = 115\text{ mA}$ , angle in degrees)

Frequency	Mag S11	Ang S11	Mag S21	Ang S21	Mag S12	Ang S12	Mag S22	Ang S22
500 MHz	0.909	-125.16	17.56	107.52	0.026	20.86	0.330	-95.81
600 MHz	0.903	-134.72	15.15	101.24	0.027	15.25	0.318	-103.71
700 MHz	0.898	-142.24	13.28	95.96	0.027	10.66	0.312	-109.87
800 MHz	0.895	-148.34	11.79	91.38	0.027	6.76	0.309	-114.77
900 MHz	0.893	-153.43	10.58	87.30	0.028	3.37	0.310	-118.75
1.0 GHz	0.891	-157.78	9.59	83.58	0.028	0.34	0.312	-122.07
1.2 GHz	0.889	-164.93	8.06	76.89	0.028	-4.92	0.320	-127.35
1.4 GHz	0.888	-170.72	6.94	70.90	0.027	-9.46	0.332	-131.53
1.6 GHz	0.888	-175.64	6.08	65.34	0.027	-13.51	0.347	-135.09
1.8 GHz	0.888	-179.99	5.41	60.10	0.027	-17.20	0.362	-138.30
2.0 GHz	0.889	176.04	4.86	55.09	0.026	-20.60	0.378	-141.33
2.2 GHz	0.889	172.35	4.42	50.24	0.025	-23.76	0.394	-144.27
2.4 GHz	0.890	168.84	4.05	45.53	0.025	-26.70	0.410	-147.16
2.6 GHz	0.891	165.46	3.73	40.93	0.024	-29.44	0.426	-150.04
2.8 GHz	0.891	162.16	3.46	36.41	0.024	-31.97	0.441	-152.92
3.0 GHz	0.892	158.90	3.23	31.95	0.023	-34.32	0.455	-155.81
3.2 GHz	0.893	155.67	3.03	27.55	0.022	-36.45	0.469	-158.73
3.4 GHz	0.893	152.43	2.85	23.19	0.021	-38.38	0.482	-161.68
3.6 GHz	0.894	149.18	2.70	18.85	0.021	-40.07	0.494	-164.66
3.8 GHz	0.894	145.89	2.56	14.53	0.020	-41.52	0.506	-167.68
4.0 GHz	0.894	142.54	2.44	10.22	0.019	-42.71	0.516	-170.74
4.1 GHz	0.895	140.85	2.38	8.07	0.019	-43.19	0.521	-172.29
4.2 GHz	0.895	139.14	2.33	5.91	0.019	-43.59	0.526	-173.85
4.3 GHz	0.895	137.40	2.28	3.75	0.018	-43.92	0.530	-175.43
4.4 GHz	0.895	135.65	2.23	1.58	0.018	-44.16	0.535	-177.02
4.5 GHz	0.895	133.88	2.18	-0.59	0.018	-44.32	0.539	-178.62
4.6 GHz	0.895	132.08	2.14	-2.77	0.017	-44.38	0.543	179.75
4.7 GHz	0.895	130.26	2.10	-4.96	0.017	-44.35	0.546	178.11
4.8 GHz	0.895	128.41	2.06	-7.15	0.017	-44.23	0.550	176.45
4.9 GHz	0.895	126.53	2.03	-9.36	0.017	-44.02	0.553	174.77
5.0 GHz	0.895	124.63	1.99	-11.58	0.016	-43.71	0.556	173.07
5.1 GHz	0.895	122.69	1.96	-13.81	0.016	-43.30	0.559	171.35
5.2 GHz	0.895	120.72	1.93	-16.05	0.016	-42.81	0.561	169.60
5.3 GHz	0.895	118.73	1.90	-18.31	0.016	-42.22	0.564	167.83
5.4 GHz	0.895	116.70	1.87	-20.59	0.016	-41.56	0.566	166.04
5.5 GHz	0.895	114.63	1.84	-22.89	0.016	-40.83	0.568	164.21
5.6 GHz	0.895	112.53	1.81	-25.20	0.016	-40.05	0.570	162.36
5.7 GHz	0.895	110.39	1.79	-27.53	0.016	-39.22	0.572	160.47
5.8 GHz	0.895	108.22	1.77	-29.89	0.016	-38.35	0.574	158.55
5.9 GHz	0.895	106.00	1.74	-32.27	0.016	-37.48	0.575	156.60
6.0 GHz	0.895	103.75	1.72	-34.67	0.016	-36.62	0.576	154.61

To download the s-parameters in s2p format, go to the [CGH55015F1/P1 Product Page](#), click on the documentation tab.

## Product Dimensions CGH55015F1 (Package Type – 440166)



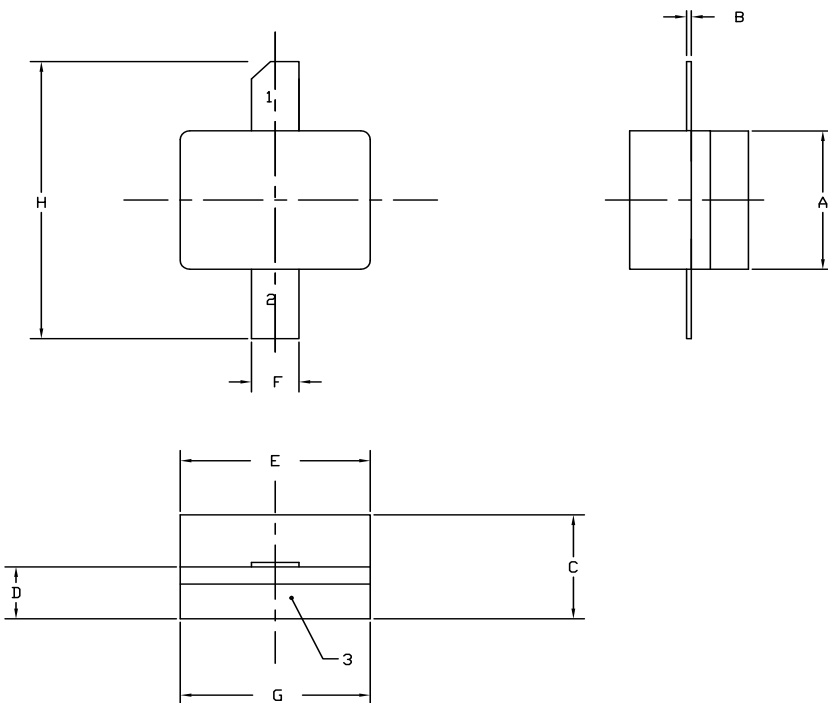
**NOTES:**

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. ADHESIVE FROM LID MAY EXTEND A MAXIMUM OF 0.020" BEYOND EDGE OF LID.
4. LID MAY BE MISALIGNED TO THE BODY OF THE PACKAGE BY A MAXIMUM OF 0.008" IN ANY DIRECTION.
5. ALL PLATED SURFACES ARE NI/AU

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.155	0.165	3.94	4.19
B	0.004	0.006	0.10	0.15
C	0.115	0.135	2.92	3.43
D	0.057	0.067	1.45	1.70
E	0.195	0.205	4.95	5.21
F	0.045	0.055	1.14	1.40
G	0.545	0.555	13.84	14.09
H	0.280	0.360	7.11	9.14
J	Ø .100		2.54	
K	0.375		9.53	

PIN 1. GATE  
PIN 2. DRAIN  
PIN 3. SOURCE

## Product Dimensions CGH55015P1 (Package Type – 440196)



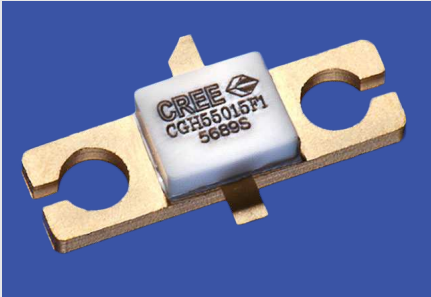
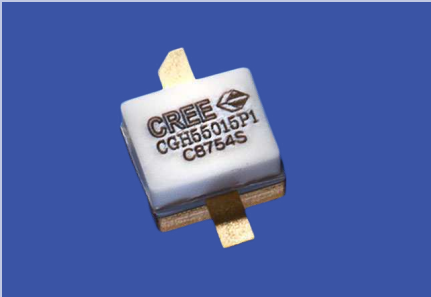
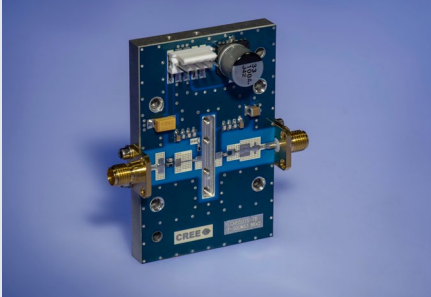
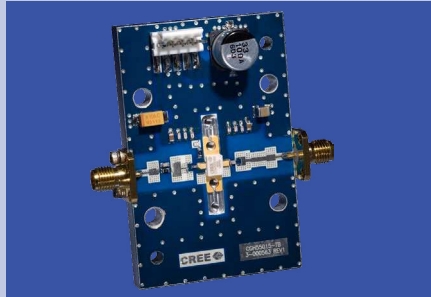
**NOTES:**

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. ADHESIVE FROM LID MAY EXTEND A MAXIMUM OF 0.020" BEYOND EDGE OF LID.
4. LID MAY BE MISALIGNED TO THE BODY OF THE PACKAGE BY A MAXIMUM OF 0.008" IN ANY DIRECTION.
5. ALL PLATED SURFACES ARE NI/AU

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.155	0.165	3.94	4.19
B	0.003	0.006	0.10	0.15
C	0.115	0.135	2.92	3.17
D	0.057	0.067	1.45	1.70
E	0.195	0.205	4.95	5.21
F	0.045	0.055	1.14	1.40
G	0.195	0.205	4.95	5.21
H	0.280	0.360	7.11	9.14

PIN 1. GATE  
PIN 2. DRAIN  
PIN 3. SOURCE

## Product Ordering Information

Order Number	Description	Unit of Measure	Image
CGH55015F1	GaN HEMT	Each	
CGH55015P1	GaN HEMT	Each	
CGH55015-TB	Test board without GaN HEMT	Each	
CGH55015-AMP	Test board with GaN HEMT installed	Each	



## Disclaimer

Specifications are subject to change without notice. Cree, Inc. believes the information contained within this data sheet to be accurate and reliable. However, no responsibility is assumed by Cree for any infringement of patents or other rights of third parties which may result from its use. No license is granted by implication or otherwise under any patent or patent rights of Cree. Cree makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose. "Typical" parameters are the average values expected by Cree in large quantities and are provided for information purposes only. These values can and do vary in different applications and actual performance can vary over time. All operating parameters should be validated by customer's technical experts for each application. Cree products are not designed, intended or authorized for use as components in applications intended for surgical implant into the body or to support or sustain life, in applications in which the failure of the Cree product could result in personal injury or death or in applications for planning, construction, maintenance or direct operation of a nuclear facility.

For more information, please contact:

Cree, Inc.  
4600 Silicon Drive  
Durham, North Carolina, USA 27703  
[www.cree.com/RF](http://www.cree.com/RF)

Sarah Miller  
Marketing  
Cree, RF Components  
1.919.407.5302

Ryan Baker  
Marketing & Sales  
Cree, RF Components  
1.919.407.7816

Tom Dekker  
Sales Director  
Cree, RF Components  
1.919.407.5639